/ Descriptions

TO-263 N MOS N-CHANNEL MOSFET in a TO-263 Plastic Package.

/ Features

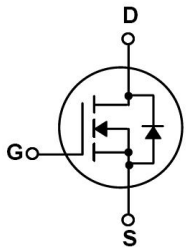
Low gate charge, low crss, fast switching.

/ Applications

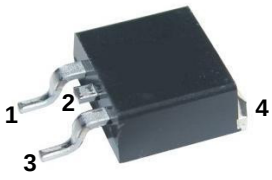
DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit



/ Pinning



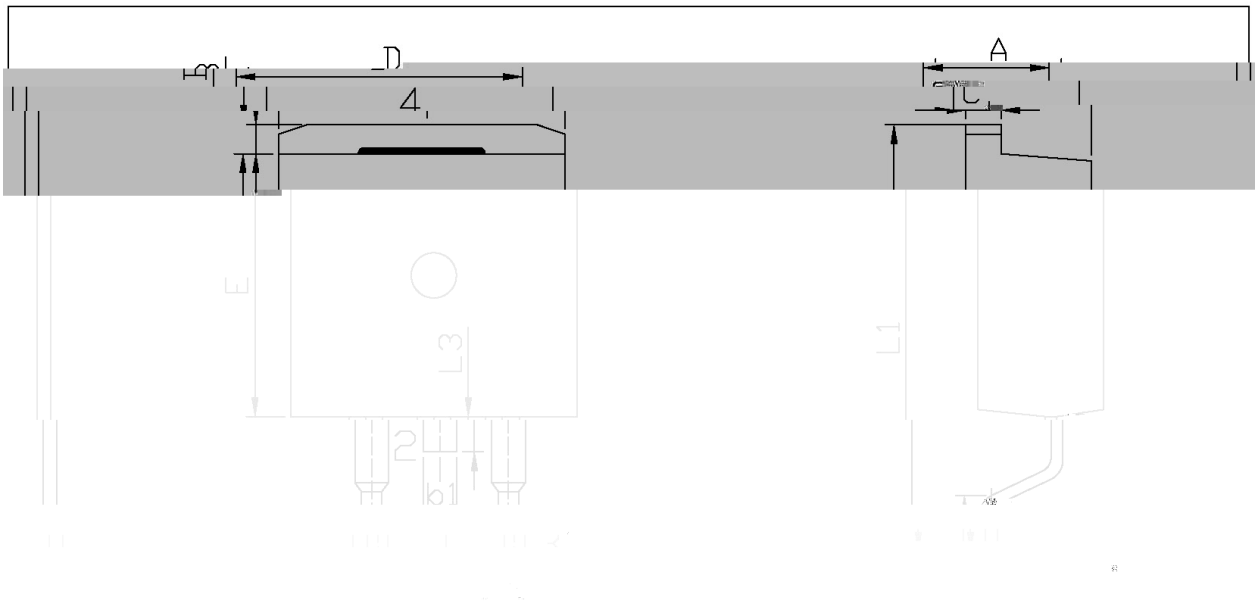
PIN1 G PIN 2,4 D PIN 3 S

/ h_{FE} Classifications & Marking

See Marking Instructions.

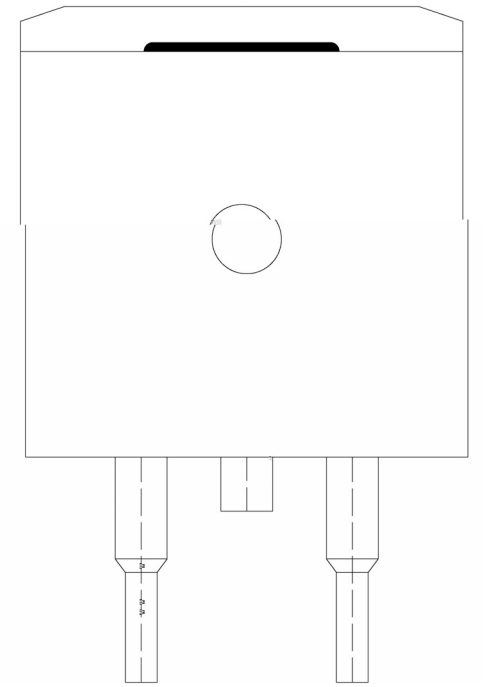
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	500	V
Drain Current	I_D(Tc=25)	8.0	A
Drain Current	I_D(Tc=100)	5.1	A

/ Package Dimensions

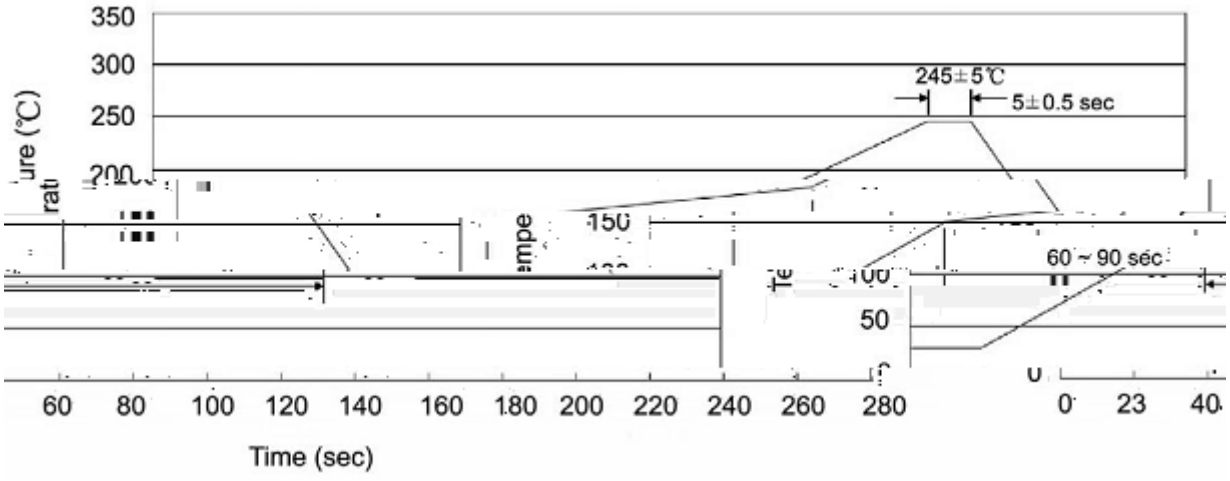


	Max			Min	Max		Min
	9.40		A	4.30	4.70	E	9.00
	2.74		B	1.00	1.40	e1	2.34
15.00	16.00		b1	1.15	1.35	L1	

/ Marking Instructions



( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

1	25	150	60	90sec;	1.Preheating:25~150 , Time:60~90sec.
2	245±5			5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3		2	10	/sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension		(unit m^3)
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
TO-263	800	1	800	5	4,000	13 ×24	360×360×50	385×2